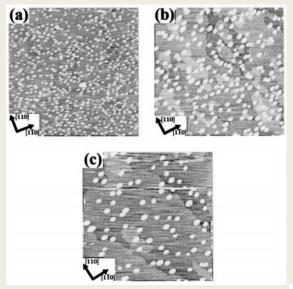
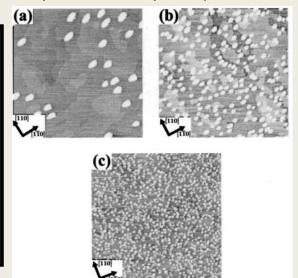
Scanning tunneling miscroscopy study of InAs islands grown on GaAs(001) substrates

■ Growth of InAs islands and wetting layers (WLs) on GaAs(001) substrates.



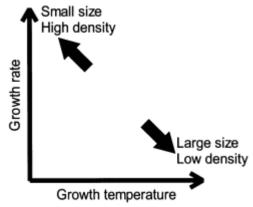
Different Temperature

- a) 420 °C (Vs=2.0 V, It=1.0 nA)
- b) 450 °C (Vs=2.0 V, It=1.0 nA)
- c) 480 °C (Vs=2.0 V, It=2.0 nA)



Different Grow Rate

- a) 0.025 ML·s-1 (450 °C, Vs=2.0 V, It=1.5 nA)
- b) 0.067 ML·s-1 (450 °C, Vs=2.0 V, It=1.0 nA)
- c) 0.133 ML·s-1 (450 °C, Vs=2.5 V, It=1.0 nA)



This figure summarizes the STM results

[&]quot;Suekane, O., Hasegawa, S., Takata, M., Okui, T., & Nakashima, H. (2002). Scanning tunneling miscroscopy study of InAs islands grown on GaAs (001) substrates. *Materials Science and Engineering:* B, 88(2-3), 158-163."